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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/698,169	10/31/2003	Sheldon Aronowitz	02-6037/LSI1P218	9839	
75	90 04/11/2005		EXAM	EXAMINER	
LSI Logic Corporation			MAI, ANH D		
1551 McCarthy Boulevard Milpitas, CA 95035			ART UNIT	PAPER NUMBER	
. ,			2814	2814	
			DATE MAILED: 04/11/2005 `		

Please find below and/or attached an Office communication concerning this application or proceeding.

		A		<u> </u>			
		Application No.	Applicant(s)	. (
Office Action Commence		10/698,169	ARONOWITZ ET AL.				
•	Office Action Summary	Examiner	Art Unit				
		Anh D. Mai	2814				
Period fo	The MAILING DATE of this communication Reply	on appears on the cover sheet w	ith the correspondence address	s			
THE - External after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICAT ansions of time may be available under the provisions of 37 SIX (6) MONTHS from the mailing date of this communicate period for reply specified above is less than thirty (30) day a period for reply is specified above, the maximum statutory re to reply within the set or extended period for reply will, be reply received by the Office later than three months after the patent term adjustment. See 37 CFR 1.704(b).	TION. CFR 1.136(a). In no event, however, may a ution. It is, a reply within the statutory minimum of thing yeriod will apply and will expire SIX (6) MOI by statute, cause the application to become Al	reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this commur BANDONED (35 U.S.C. § 133).	nication.			
Status							
1)⊠	Responsive to communication(s) filed or	n 14 March 2005					
	_	This action is non-final.	•				
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dispositi	ion of Claims						
5)□ 6)⊠ 7)□	Claim(s) <u>2-20</u> is/are pending in the appli 4a) Of the above claim(s) <u>3,7-9 and 12-2</u> Claim(s) is/are allowed. Claim(s) <u>2,4-6,10 and 11</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction	<u>0</u> is/are withdrawn from conside	eration.				
Applicati	on Papers						
10)⊠	The specification is objected to by the Ex The drawing(s) filed on <u>31 October 2003</u> Applicant may not request that any objection Replacement drawing sheet(s) including the The oath or declaration is objected to by	is/are: a) accepted or b) of to the drawing(s) be held in abeya correction is required if the drawing	nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.	• •			
Priority ι	ınder 35 U _. S.C. § 119						
a)	Acknowledgment is made of a claim for f All b) Some * c) None of: 1. Certified copies of the priority doc 2. Certified copies of the priority doc 3. Copies of the certified copies of the application from the International I	uments have been received. uments have been received in A le priority documents have been Bureau (PCT Rule 17.2(a)).	Application No received in this National Stag	ge			
Attachmen		∆\ □ 1=••==:::					
2) 🔲 Notic 3) 🔲 Inform	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-9 nation Disclosure Statement(s) (PTO-1449 or PTO r No(s)/Mail Date	Paper No(Summary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152))			

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Status of the Claims

1. Amendment filed March 14, 2005 has been entered. Claim 1 has been cancelled. Claims 2, 10 and 11 have been amended. Claims 2-20 are pending. Claims 3, 7-9 and 12-20 have been withdrawn.

Drawings

2. The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the "semiconductor integrated circuit" must be shown or the feature(s) canceled from the claim(s). No new matter should be entered.

Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will

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be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

A single device can not be the same as a semiconductor integrated circuit.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 2, 4-6, 10 and 11 are rejected under 35 U.S.C. 102(b) as being anticipated by Yamamoto (U.S. Pub. No. 2002/0153579).

With respect to claim 2, Yamamoto teaches a semiconductor memory device as claimed including:

a semiconductor substrate (1);

a dielectric gate stack formed on a channel region of the substrate (1), the dielectric gate stack having a top portion and a bottom portion;

the dielectric gate stack including an electron trapping layer (4) formed of electron trapping material that is zirconium oxide (ZrO₂). (See Fig. 5A-C).

With respect to claim 4, the dielectric gate stack of Yamamoto includes a first layer (17) of dielectric material and a second layer (17) of dielectric material configured such that the first

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layer (17) of dielectric material is formed on the channel region of the substrate (1) and the electron trapping layer (4) is formed on the first layer (17) of dielectric material and wherein the second layer (17) of dielectric material is formed on the electron trapping layer (4).

With respect to claim 5, the first layer (17) of dielectric material and the second layer (17) of dielectric material of Yamamoto are each comprised of silicon oxide. (See Fig. 5C).

With respect to claim 6, the first layer (17) of dielectric material of Yamamoto can be formed of a different dielectric material than the second layer (6) of dielectric material. (See Fig. 5B).

With respect to claim 10, the memory device of Yamamoto is formed as part of a semiconductor integrated circuit.

With respect to claim 11, Yamamoto teaches a semiconductor memory device as claimed including:

a semiconductor substrate (1) having a source and a drain (2) separated by a channel region;

a first dielectric layer (17) formed on the channel region of the substrate (1); an electron trapping layer (4) formed on the first dielectric layer (17), the electron trapping layer (4) formed of an electron trapping material that is zirconium oxide (ZrO₂);

a second dielectric layer (17) formed on the electron trapping layer (4); and

a gate electrode (5b) connected with the second dielectric layer (17). (See Fig. 5C).

Response to Arguments

- 4. Regarding the drawing, Fig. 5 does not anywhere resemblance an integrated circuit.
- 5. Applicant's arguments with respect to pending claims have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

6. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Anh D. Mai whose telephone number is (571) 272-1710. The examiner can normally be reached on 9:00AM-5:00PM.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

ANH D. MAI DDIMADV EYAAAINE

April 7, 2005